

International
IR Rectifier
 INSULATED GATE BIPOLAR TRANSISTOR

PD - 95645A

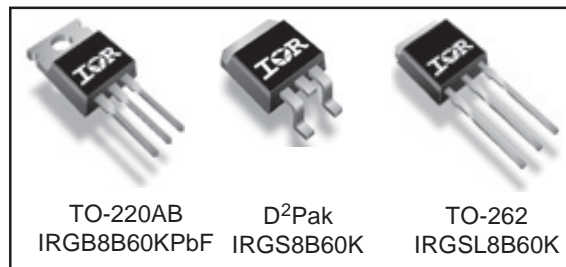
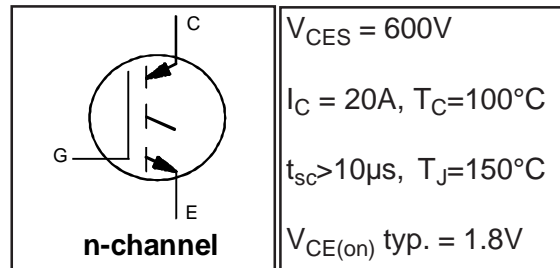
IRGB8B60KPbF
IRGS8B60KPbF
IRGSL8B60KPbF

Features

- Low VCE (on) Non Punch Through IGBT Technology.
- 10µs Short Circuit Capability.
- Square RBSOA.
- Positive VCE (on) Temperature Coefficient.
- Lead-Free.

Benefits

- Benchmark Efficiency for Motor Control.
- Rugged Transient Performance.
- Low EMI.
- Excellent Current Sharing in Parallel Operation.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	28	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	19	
I_{CM}	Pulse Collector Current (Ref.Fig.C.T.5)	56	
I_{LM}	Clamped Inductive Load current ①	56	
V_{GE}	Gate-to-Emitter Voltage	±20	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	167	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	83	
T_J	Operating Junction and	-55 to +175	°C
T_{STG}	Storage Temperature Range		
	Storage Temperature Range, for 10 sec.		

Thermal / Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case- IGBT	—	—	0.90	°C/W
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount ②	—	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, Steady State) ③	—	—	40	
	Weight	—	1.44	—	g

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V _{GE} = 0V, I _C = 500μA	
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	0.57	—	V/°C	V _{GE} = 0V, I _C = 1mA (25°C-150°C)	
V _{CE(on)}	Collector-to-Emitter Voltage	—	1.8	2.2	V	I _C = 8.0A, V _{GE} = 15V, T _J = 25°C	5,6,7
		—	2.2	2.5		I _C = 8.0A, V _{GE} = 15V, T _J = 150°C	8,9,10
		—	2.3	2.6		I _C = 8.0A, V _{GE} = 15V, T _J = 175°C	
V _{GE(th)}	Gate Threshold Voltage	3.5	4.5	5.5		V _{CE} = V _{GE} , I _C = 250μA	8,9,10,
ΔV _{GE(th)} /ΔT _J	Threshold Voltage temp. coefficient	—	-9.5	—	mV/°C	V _{CE} = V _{GE} , I _C = 1mA (25°C-125°C)	11
g _{fe}	Forward Transconductance	—	3.7	—	S	V _{CE} = 50V, I _C = 8.0A, PW = 80μs	
I _{CES}	Zero Gate Voltage Collector Current	—	1.0	150	μA	V _{GE} = 0V, V _{CE} = 600V	
		—	200	500		V _{GE} = 0V, V _{CE} = 600V, T _J = 150°C	
		—	800	1320		V _{GE} = 0V, V _{CE} = 600V, T _J = 175°C	
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V	

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
Q _g	Total Gate Charge (turn-on)	—	29	—	nC	I _C = 8.0A	17
Q _{ge}	Gate-to-Emitter Charge (turn-on)	—	3.7	—		V _{CC} = 480V	CT1
Q _{gc}	Gate-to-Collector Charge (turn-on)	—	14	—		V _{GE} = 15V	
E _{on}	Turn-On Switching Loss	—	160	268	μJ	I _C = 8.0A, V _{CC} = 400V	CT4
E _{off}	Turn-Off Switching Loss	—	160	268		V _{GE} = 15V, R _G = 50Ω, L = 1.1mH	
E _{tot}	Total Switching Loss	—	320	433		T _J = 25°C ⊕	
t _{d(on)}	Turn-On delay time	—	23	27	ns	I _C = 8.0A, V _{CC} = 400V	CT4
t _r	Rise time	—	22	26		V _{GE} = 15V, R _G = 50Ω, L = 1.1mH	
t _{d(off)}	Turn-Off delay time	—	140	150		T _J = 25°C	
t _f	Fall time	—	32	42			
E _{on}	Turn-On Switching Loss	—	220	330	μJ	I _C = 8.0A, V _{CC} = 400V	CT4
E _{off}	Turn-Off Switching Loss	—	270	381		V _{GE} = 15V, R _G = 50Ω, L = 1.1mH	12,14
E _{tot}	Total Switching Loss	—	490	608		T _J = 150°C ⊕	WF1,WF2
t _{d(on)}	Turn-On delay time	—	22	27	ns	I _C = 8.0A, V _{CC} = 400V	13,15
t _r	Rise time	—	21	25		V _{GE} = 15V, R _G = 50Ω, L = 1.1mH	CT4
t _{d(off)}	Turn-Off delay time	—	180	198		T _J = 150°C	WF1
t _f	Fall time	—	40	56			WF2
C _{ies}	Input Capacitance	—	440	—	pF	V _{GE} = 0V	16
C _{oes}	Output Capacitance	—	38	—		V _{CC} = 30V	
C _{res}	Reverse Transfer Capacitance	—	16	—		f = 1.0MHz	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T _J = 150°C, I _C = 34A, V _p = 600V V _{CC} =500V, V _{GE} = +15V to 0V, R _G = 50Ω	4 CT2
SCSOA	Short Circuit Safe Operating Area	10	—	—	μs	T _J = 150°C, V _p = 600V, R _G = 100Ω V _{CC} =360V, V _{GE} = +15V to 0V	CT3 WF3

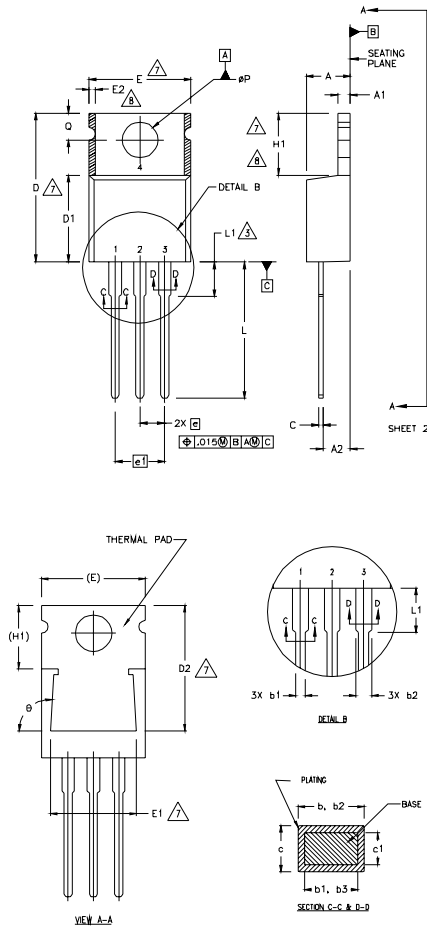
Notes ⊕ to ⊕ are on page 13.

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TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5 DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
- 6 CONTROLLING DIMENSION : INCHES.
- 7 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8 DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

IGBTs CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.82	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.04	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.96	.015	.038	5
b2	1.15	1.77	.045	.070	
b3	1.15	1.73	.045	.068	
c	0.36	0.61	.014	.024	
c1	0.56	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	12.19	12.88	.480	.507	7
E	9.66	10.66	.380	.420	4,7
E1	8.38	8.89	.330	.350	7
e	2.54 BSC		.100 BSC		
e1	5.08		.200 BSC		
H1	5.85	6.55	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	-	6.35	-	.250	3
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	
ø	90°-93°		90°-93°		

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line position indicates "Lead-Free"

